International
IOR Rectifier

SMPS MOSFET

IRLR8203PbF
IRLU8203PbF

HEXFET® Power MOSFET

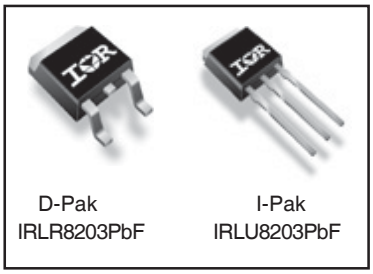
Applications

- High Frequency Isolated DC-DC Converters with Synchronous Rectification for Telecom and Industrial Use
- High Frequency Buck Converters for Computer Processor Power
- Lead-Free

Benefits

- Ultra-Low Gate Impedance
- Very Low RDS(on) at 4.5V V_{GS}
- Fully Characterized Avalanche Voltage and Current

V_{DSS}	$R_{DS(on)}$ max	I_D
30V	6.8mΩ	110A④



D-Pak
IRLR8203PbF

I-Pak
IRLU8203PbF

Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	110 ④	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	76 ④	
I_{DM}	Pulsed Drain Current①	120	
P_D @T_C = 25°C	Maximum Power Dissipation③	140	W
P_D @T_C = 100°C	Maximum Power Dissipation③	69	W
	Linear Derating Factor	0.92	W/°C
T_J , T_{STG}	Junction and Storage Temperature Range	-55 to + 175	°C

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	——	1.09	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount)*	——	50	
$R_{\theta JA}$	Junction-to-Ambient	——	110	

* When mounted on 1" square PCB (FR-4 or G-10 Material) .
For recommended footprint and soldering techniques refer to application note #AN-994

Notes ① through ④ are on page 10

Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	30	——	——	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	——	0.027	——	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	——	5.6	6.8	mΩ	V_{GS} = 10V, I_D = 15A ③
		——	7.1	9.0		V_{GS} = 4.5V, I_D = 12A ③
$V_{GS(th)}$	Gate Threshold Voltage	1.0	——	3.0	V	V_{DS} = V_{GS}, I_D = 250µA
I_{DSS}	Drain-to-Source Leakage Current	——	——	20	µA	V_{DS} = 24V, V_{GS} = 0V
		——	——	100		V_{DS} = 24V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Forward Leakage	——	——	200	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	——	——	-200		V_{GS} = -20V

Dynamic @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	35	——	——	S	V_{DS} = 15V, I_D = 12A
Q_g	Total Gate Charge	——	33	50	nC	I_D = 12A
Q_{gs}	Gate-to-Source Charge	——	5.7	8.5		V_{DS} = 24V
Q_{gd}	Gate-to-Drain ("Miller") Charge	——	17	25		V_{GS} = 4.5V ③
Q_{oss}	Output Gate Charge	——	23	34		V_{GS} = 0V, V_{DS} = 10V
$t_{d(on)}$	Turn-On Delay Time	——	15	——	ns	V_{DD} = 15V
t_r	Rise Time	——	99	——		I_D = 12A
$t_{d(off)}$	Turn-Off Delay Time	——	30	——		R_G = 6.8Ω
t_f	Fall Time	——	69	——		V_{GS} = 4.5V ③
C_{iss}	Input Capacitance	——	2430	——	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	——	1200	——		V_{DS} = 15V
C_{rss}	Reverse Transfer Capacitance	——	250	——		f = 1.0MHz

Avalanche Characteristics

Symbol	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②	——	310	mJ
I_{AR}	Avalanche Current①	——	30	A

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	——	——	110④	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	——	——	120		
V_{SD}	Diode Forward Voltage	——	0.75	1.3	V	T_J = 25°C, I_S = 12A, V_{GS} = 0V ③
		——	0.65	——		T_J = 125°C, I_S = 12A, V_{GS} = 0V ③
t_{rr}	Reverse Recovery Time	——	48	72	ns	T_J = 25°C, I_F = 12A, V_R=15V
Q_{rr}	Reverse Recovery Charge	——	62	92	nC	di/dt = 100A/µs ③
t_{rr}	Reverse Recovery Time	——	49	74	ns	T_J = 125°C, I_F = 12A, V_R=15V
Q_{rr}	Reverse Recovery Charge	——	67	100	nC	di/dt = 100A/µs ③

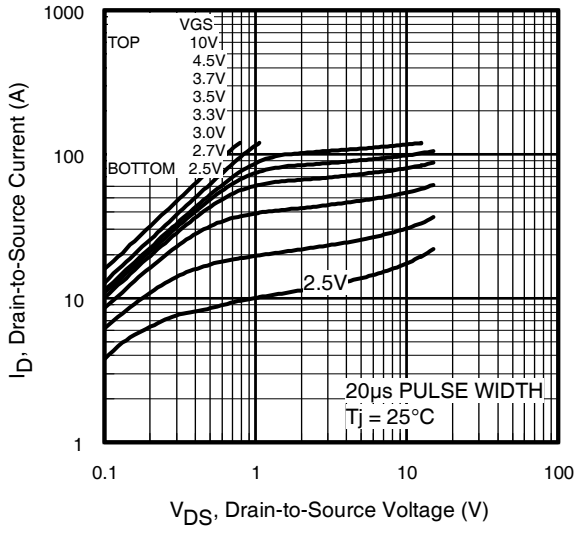


Fig 1. Typical Output Characteristics

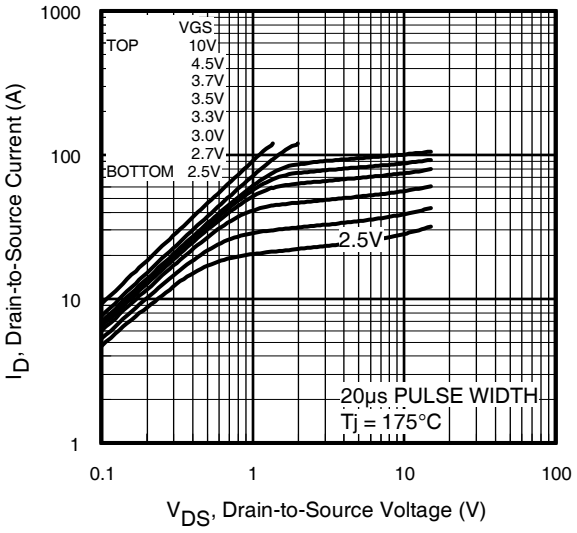


Fig 2. Typical Output Characteristics

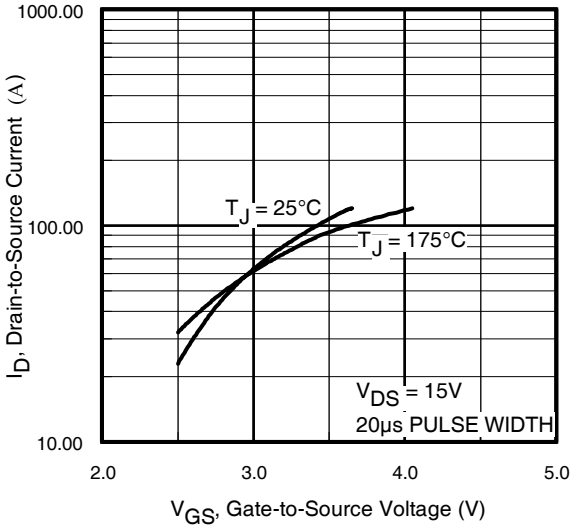


Fig 3. Typical Transfer Characteristics

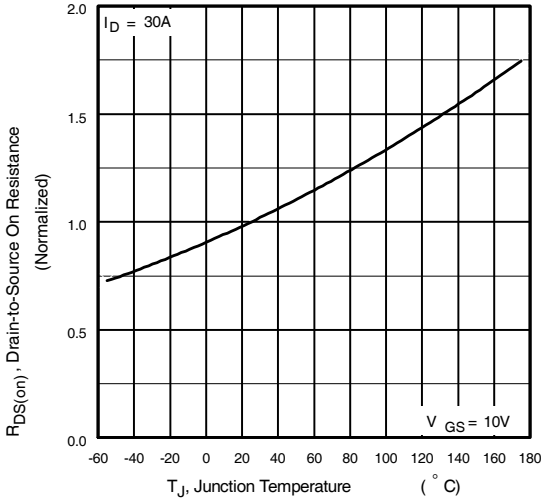


Fig 4. Normalized On-Resistance Vs. Temperature

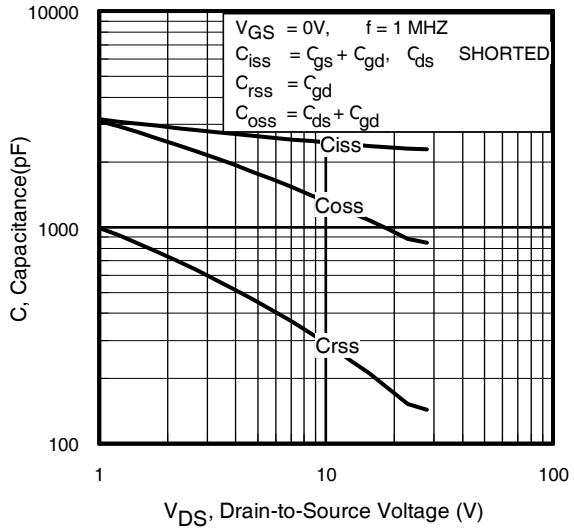


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

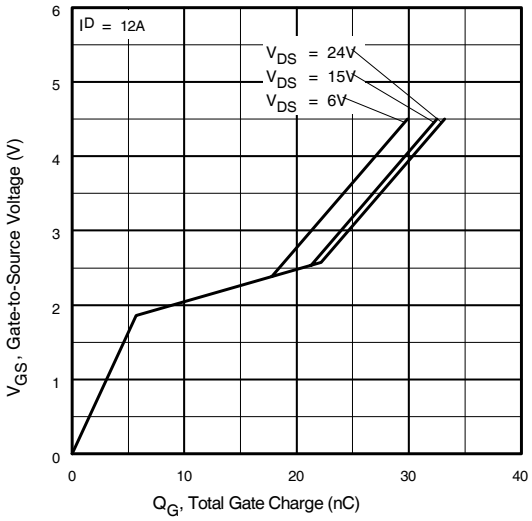


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

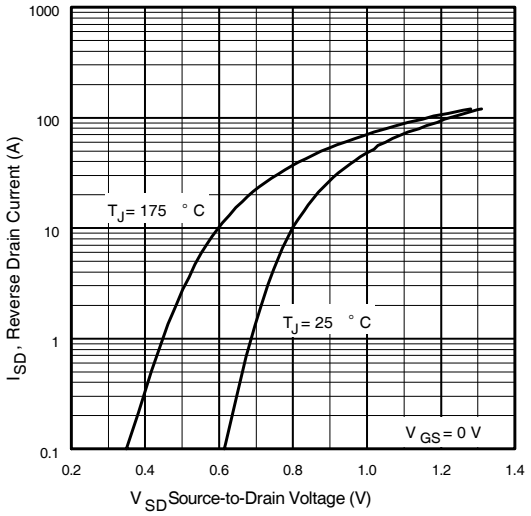


Fig 7. Typical Source-Drain Diode Forward Voltage

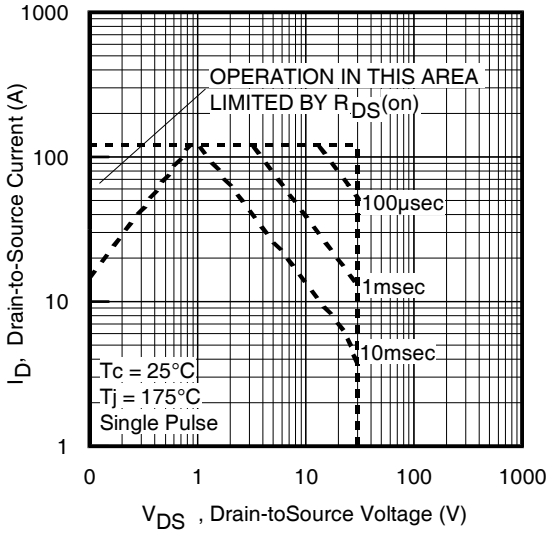


Fig 8. Maximum Safe Operating Area

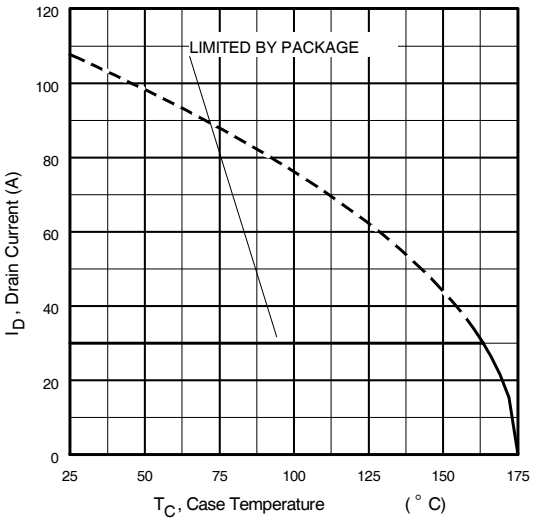


Fig 9. Maximum Drain Current Vs. Case Temperature

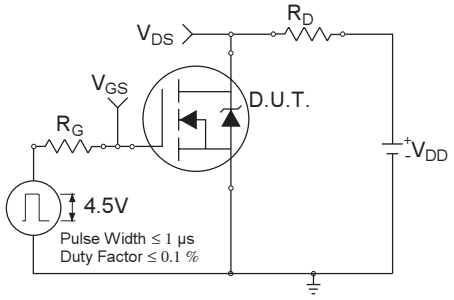


Fig 10a. Switching Time Test Circuit

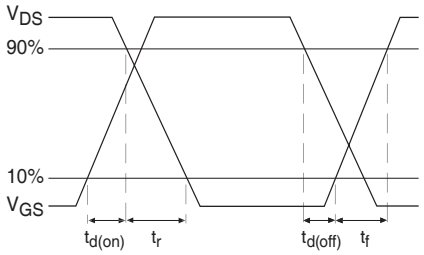


Fig 10b. Switching Time Waveforms

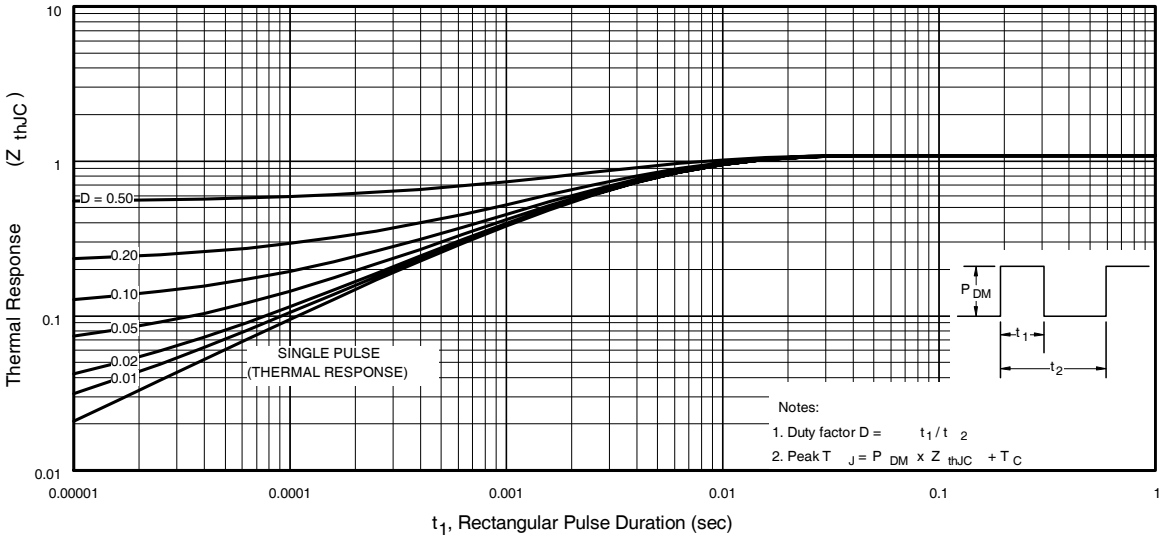


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

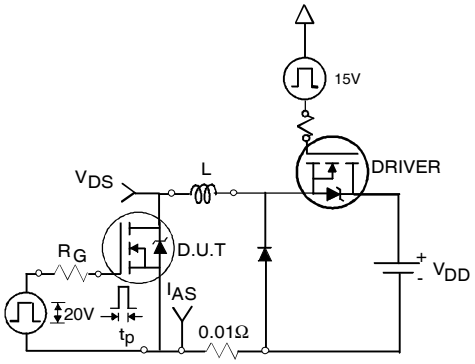


Fig 12a. Unclamped Inductive Test Circuit

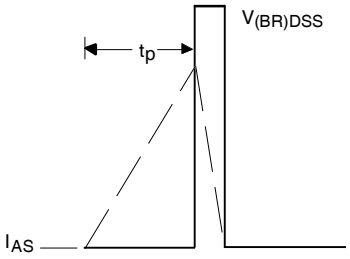


Fig 12b. Unclamped Inductive Waveforms

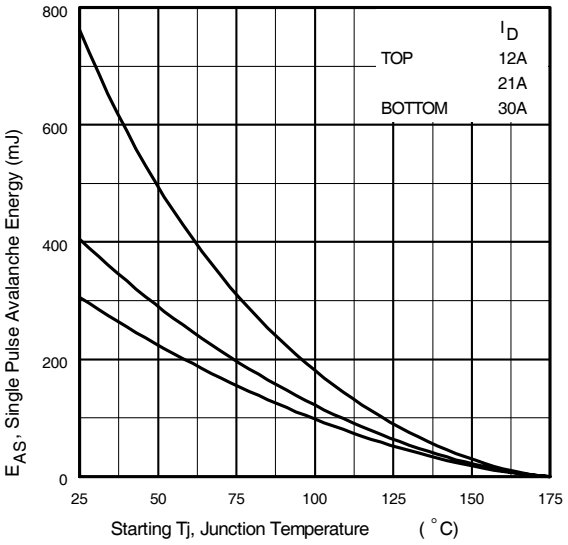


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

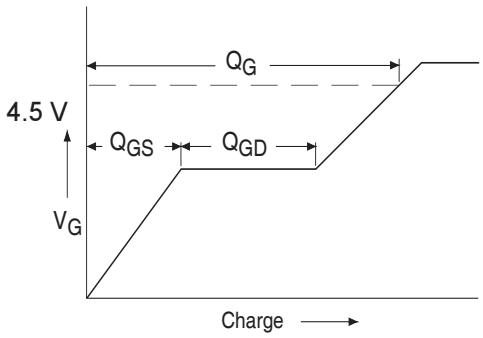


Fig 13a. Basic Gate Charge Waveform

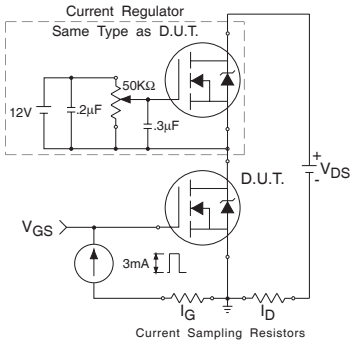


Fig 13b. Gate Charge Test Circuit

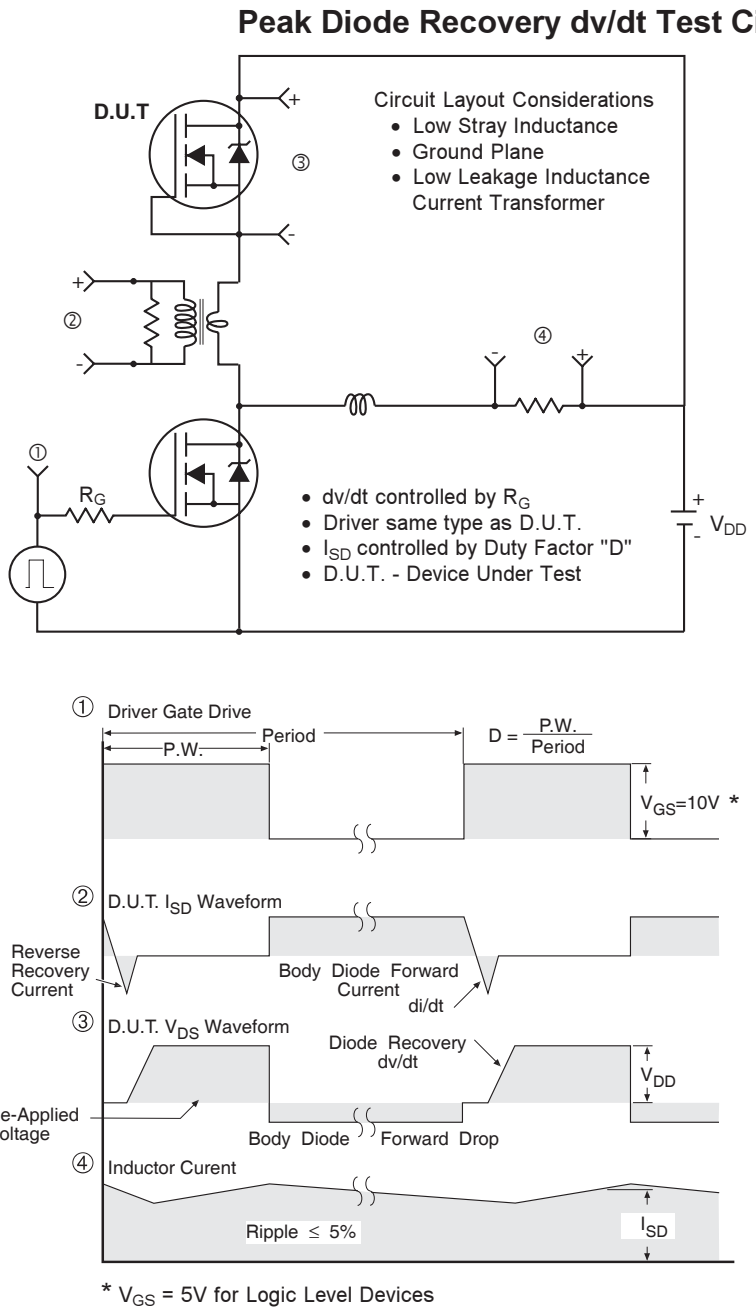
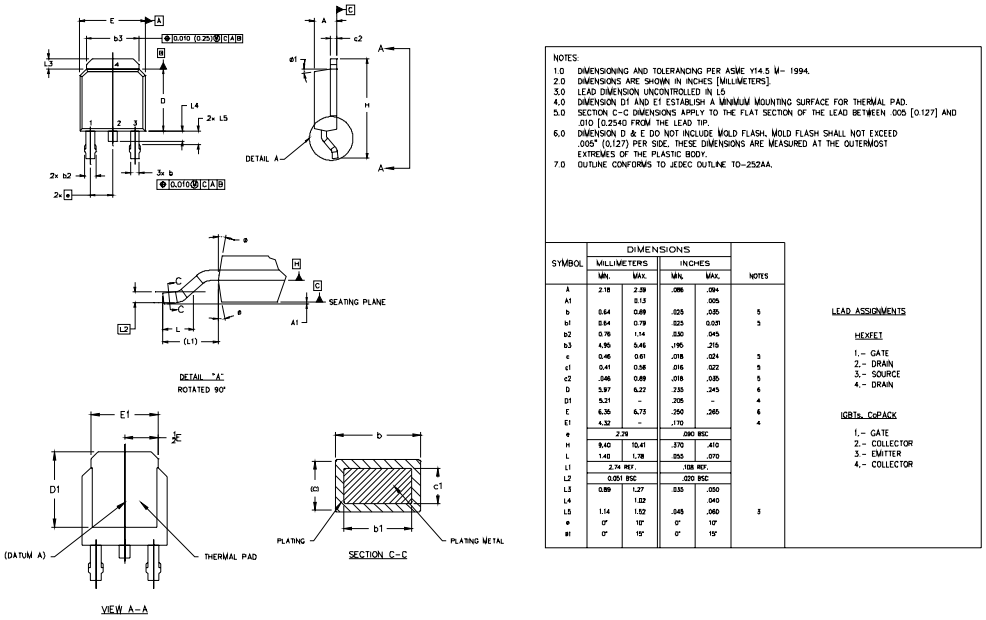


Fig 14. For N-Channel HEXFET® Power MOSFETs

D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



NOTES:
1.0 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
2.0 DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
3.0 LEAD DIMENSION UNCONTROLLED IN L5.
4.0 DIMENSION D1 AND E1 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
5.0 SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 [0.127] AND .010 [0.254Ø] FROM THE LEAD TIP.
6.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
7.0 OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1	0	0.13	0	.005	
b	0.64	0.89	.025	.035	5
b1	0.64	0.79	.025	0.031	5
b2	0.76	1.14	.030	.045	
b3	4.95	5.46	.195	.215	
c	0.46	0.61	.018	.024	5
c1	0.41	0.56	.016	.022	5
c2	.046	0.89	.018	.035	5
D	5.97	6.22	.235	.245	6
D1	5.21	-	.205	-	4
E	6.35	6.73	.250	.265	6
E1	4.32	-	.170		4
e	2.29		.090 BSC		
H	9.40	10.41	.370	.410	
L	1.40	1.78	.055	.070	
L1	2.74 REF.		.108 REF.		
L2	0.051 BSC		.020 BSC		
L3	0.89	1.27	.035	.050	
L4		1.02		.040	
L5	1.14	1.52	.045	.060	3
ø	0°	10°	0°	10°	
ø1	0°	15°	0°	15°	

LEAD ASSIGNMENTS

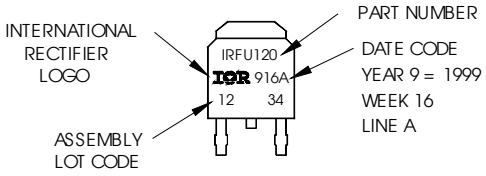
HEXFET
1.- GATE
2.- DRAIN
3.- SOURCE
4.- DRAIN

IGBTs, CoPACK
1.- GATE
2.- COLLECTOR
3.- EMITTER
4.- COLLECTOR

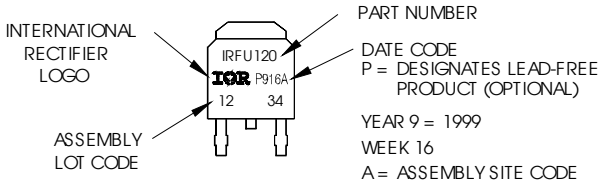
D-Pak (TO-252AA) Part Marking Information

EXAMPLE: THIS IS AN IRFR120
WITH ASSEMBLY
LOT CODE 1234
ASSEMBLED ON WW 16, 1999
IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position
indicates "Lead-Free"

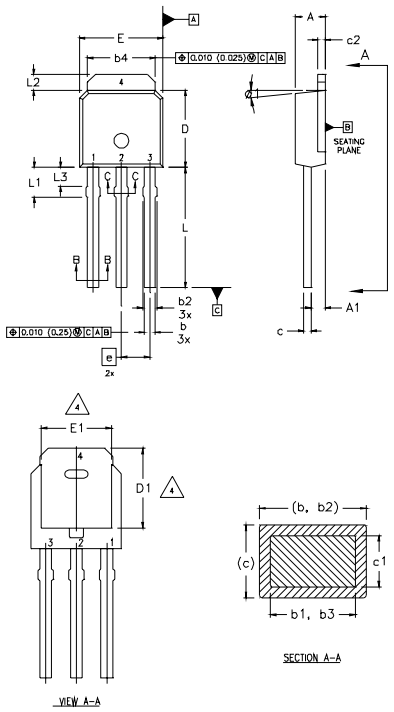


OR



I-Pak (TO-251AA) Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
2 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
4 THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.
5 LEAD DIMENSION UNCONTROLLED IN L3.
6 DIMENSION b1, b3 APPLY TO BASE METAL ONLY.
7 OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA.
8 CONTROLLING DIMENSION : INCHES.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	0.086	.094	
A1	0.89	1.14	0.035	0.045	
b	0.64	0.89	0.025	0.035	
b1	0.64	0.79	0.025	0.031	4
b2	0.76	1.14	0.030	0.045	
b3	0.76	1.04	0.030	0.041	
b4	5.00	5.46	0.195	0.215	4
c	0.46	0.61	0.018	0.024	
c1	0.41	0.56	0.016	0.022	
c2	.046	0.86	0.018	0.035	
D	5.97	6.22	0.235	0.245	3, 4
D1	5.21	-	0.205	-	4
E	6.35	6.73	0.250	0.265	3, 4
E1	4.32	-	0.170	-	4
e	2.29		0.090 BSC		
L	8.89	9.60	0.350	0.380	
L1	1.91	2.29	0.075	0.090	
L2	0.89	1.27	0.035	0.050	4
L3	1.14	1.52	0.045	0.060	5
ø1	0°	15°	0°	15°	

LEAD ASSIGNMENTS

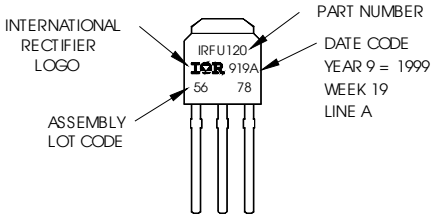
HEXFET

1.– GATE
2.– DRAIN
3.– SOURCE
4.– DRAIN

I-Pak (TO-251AA) Part Marking Information

EXAMPLE: THIS IS AN IRFU120
WITH ASSEMBLY
LOT CODE 5678
ASSEMBLED ON WW 19, 1999
IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position indicates "Lead-Free"



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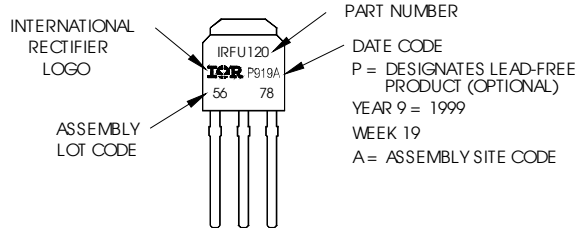
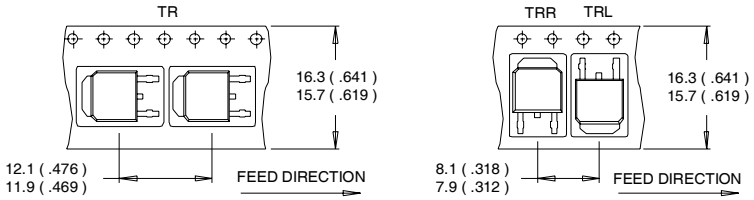
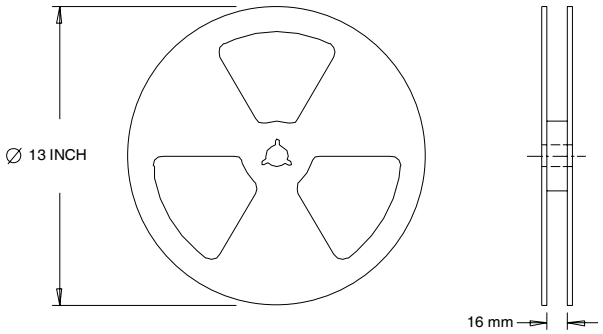


D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :
1. OUTLINE CONFORMS TO EIA-481.

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Starting T_J = 25°C, L = 0.68mH R_G = 25Ω, I_{AS} = 30A.

③ Pulse width ≤ 400µs; duty cycle ≤ 2%.

④Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 30A.

Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market.
Qualification Standards can be found on IR's Web site.

International
IOR Rectifier

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TAC Fax: (310) 252-7903
Visit us at www.irf.com for sales contact information.12/04

Note: For the most current drawings please refer to the IR website at:
http://www.irf.com/package/